



SANYO Semiconductors

DATA SHEET

2SA1479 / 2SC3789 — PNP / NPN Epitaxial Planar Silicon Transistors

High-Definition CRT Display Video Output Applications

Applications

- High-definition CRT display.
- Color TV chroma output, high breakdown voltage drivers.

Features

- High breakdown voltage : $V_{CEO} \geq 300V$.
- Excellent high frequency characteristic : $C_{re} = 1.8pF$ (typ).
- Adoption of MBIT process.
- No insulator required for mounting, which contributes to reducing the cost and the number of manufacturing processes.
- Plastic-covered heat sink facilitating high-density mounting.
- Directly interchangeable with TO-126 because the package is designed based on the conventional package dimensions.

Specifications () : 2SA1479

Absolute Maximum Ratings at $T_a = 25^\circ C$

| Parameter | Symbol | Conditions | Ratings | Unit |
|------------------------------|-----------|--------------------|-------------|------------|
| Collector-to-Base Voltage | V_{CBO} | | (-)300 | V |
| Collector-to-Emitter Voltage | V_{CEO} | | (-)300 | V |
| Emitter-to-Base Voltage | V_{EBO} | | (-)5 | V |
| Collector Current | I_C | | (-)100 | mA |
| Collector Current (Pulse) | I_{CP} | | (-)200 | mA |
| Collector Dissipation | P_C | | 1.5 | W |
| | | $T_c = 25^\circ C$ | 7 | W |
| Junction Temperature | T_j | | 150 | $^\circ C$ |
| Storage Temperature | T_{stg} | | -55 to +150 | $^\circ C$ |

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2SA1479 / 2SC3789

Electrical Characteristics at Ta=25°C

| Parameter | Symbol | Conditions | Ratings | | | Unit |
|---|---------------|----------------------------------|---------|----------|--------|---------|
| | | | min | typ | max | |
| Collector Cutoff Current | I_{CBO} | $V_{CB} = (-)200V, I_E = 0A$ | | | (-)0.1 | μA |
| Emitter Cutoff Current | I_{EBO} | $V_{EB} = (-)4V, I_C = 0A$ | | | (-)0.1 | μA |
| DC Current Gain | h_{FE} | $V_{CE} = (-)10V, I_C = (-)10mA$ | 40* | | 320* | |
| Gain-Bandwidth Product | f_T | $V_{CE} = (-)30V, I_C = (-)10mA$ | | 70 | | MHz |
| Collector-to-Emitter Saturation Voltage | $V_{CE(sat)}$ | $I_C = (-)20mA, I_B = (-)2mA$ | | | (-)0.6 | V |
| Base-to-Emitter Saturation Voltage | $V_{BE(sat)}$ | $I_C = (-)20mA, I_B = (-)2mA$ | | | (-)1.0 | V |
| Collector-to-Base Breakdown Voltage | $V_{(BR)CBO}$ | $I_C = (-)10\mu A, I_E = 0A$ | (-)300 | | | V |
| Collector-to-Emitter Breakdown Voltage | $V_{(BR)CEO}$ | $I_C = (-)1mA, R_{BE} = \infty$ | (-)300 | | | V |
| Emitter-to-Base Breakdown Voltage | $V_{(BR)EBO}$ | $I_E = (-)10\mu A, I_C = 0A$ | (-)5 | | | V |
| Output Capacitance | Cob | $V_{CB} = (-)30V, f = 1MHz$ | | (3.1)2.6 | | pF |
| Reverse Transfer Capacitance | Cre | $V_{CB} = (-)30V, f = 1MHz$ | | (2.3)1.8 | | pF |

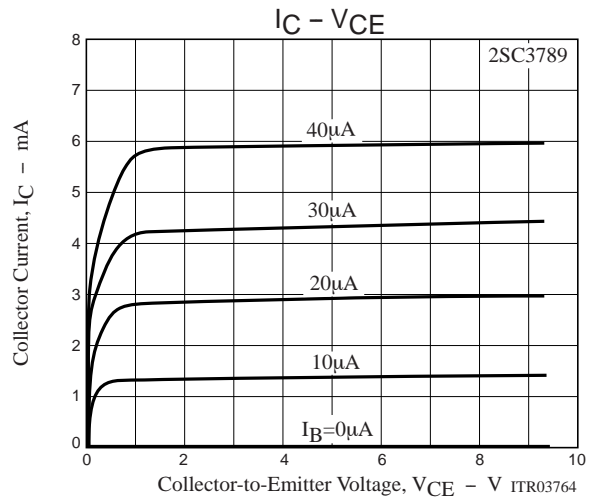
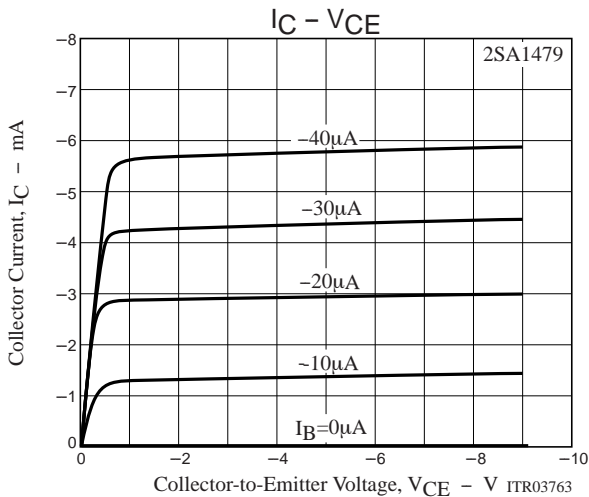
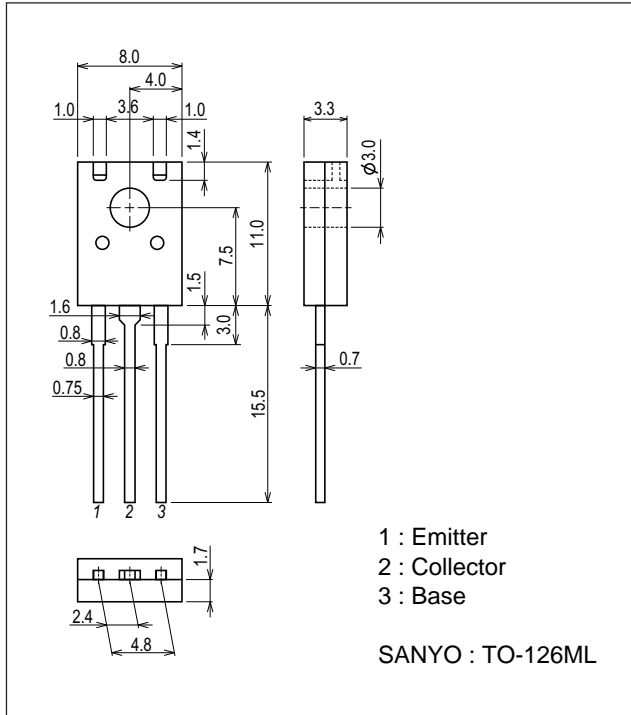
* : The 2SA1479 / 2SC3789 are classified by 10mA h_{FE} as follows:

| Rank | C | D | E | F |
|----------|----------|-----------|------------|------------|
| h_{FE} | 40 to 80 | 60 to 120 | 100 to 200 | 160 to 320 |

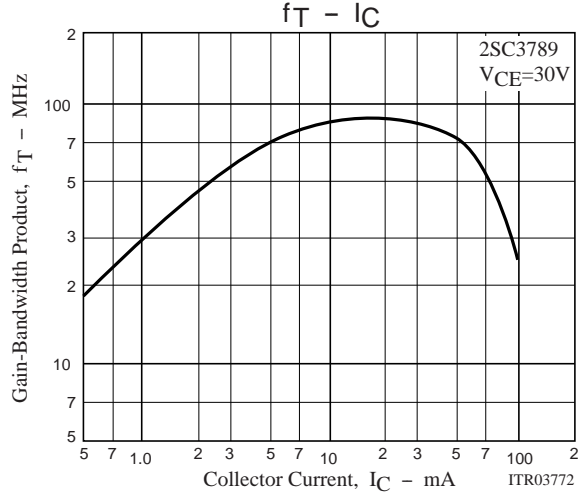
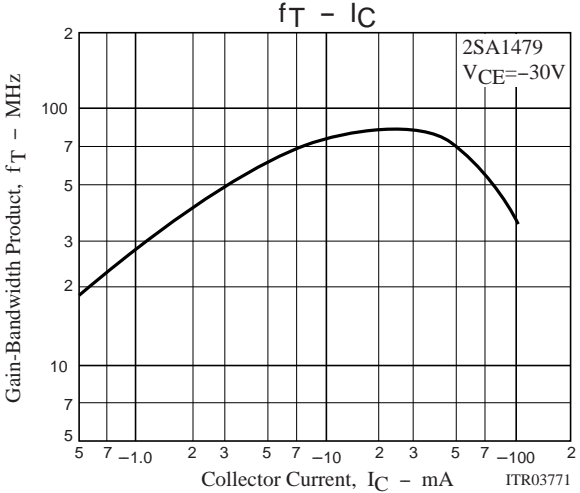
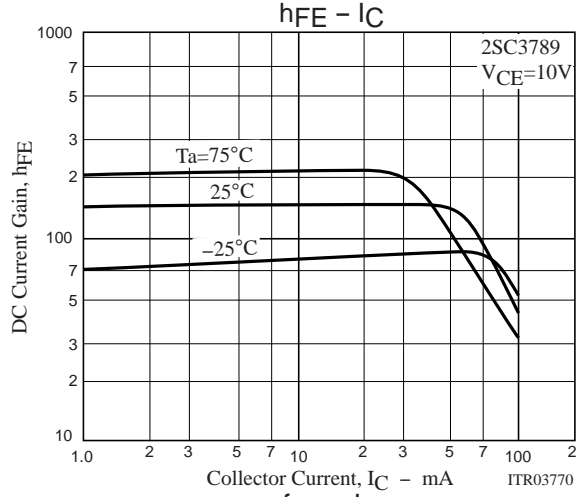
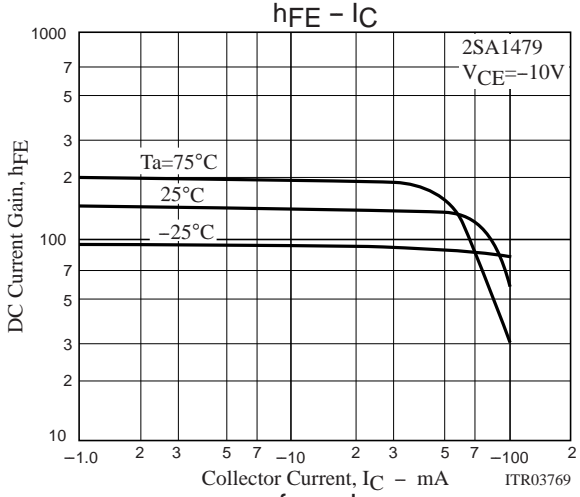
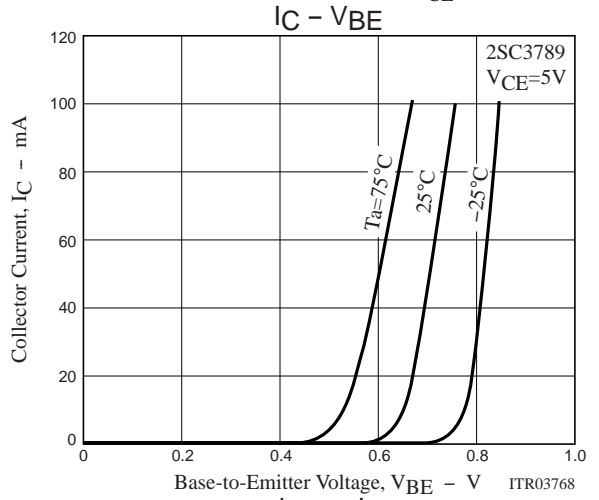
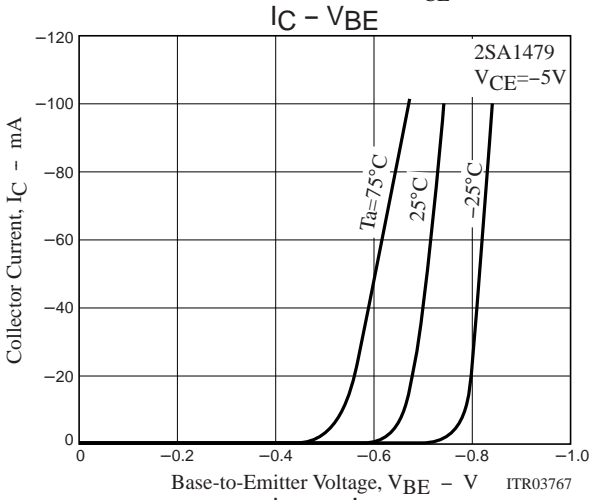
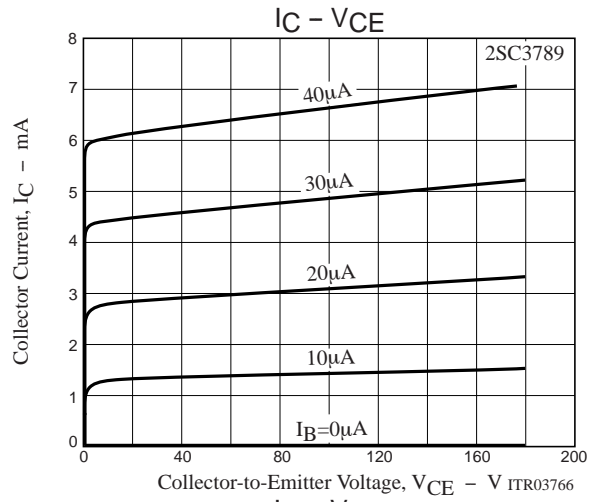
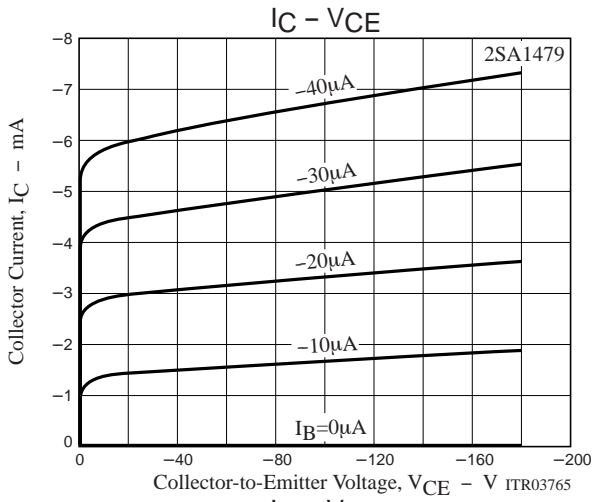
Package Dimensions

unit : mm (typ)

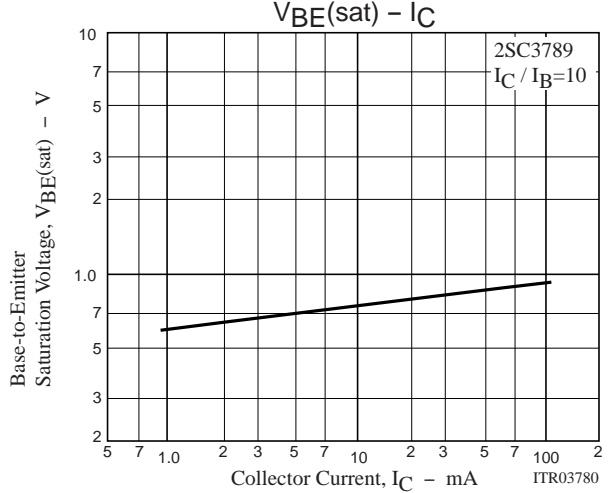
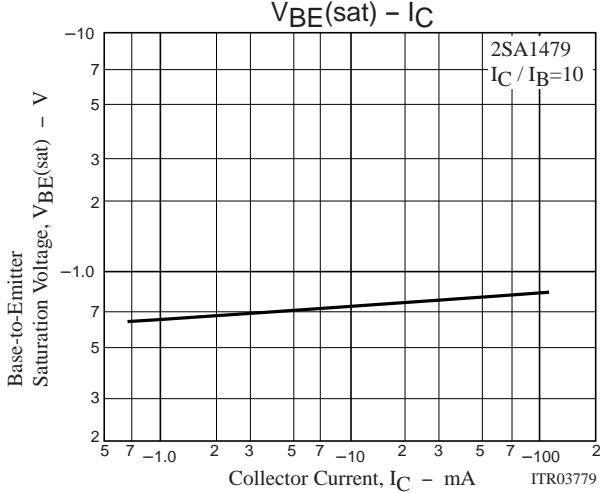
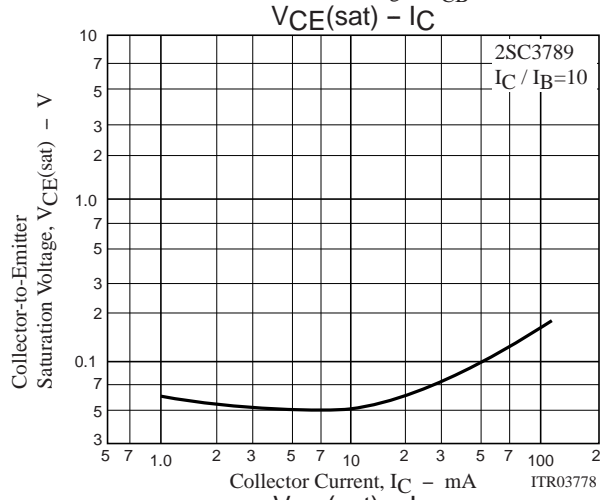
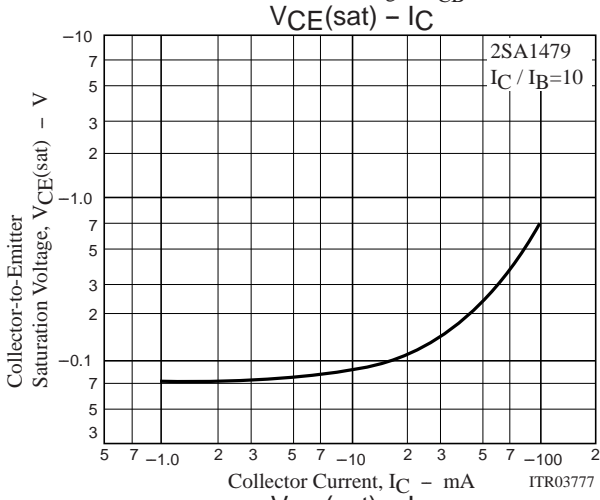
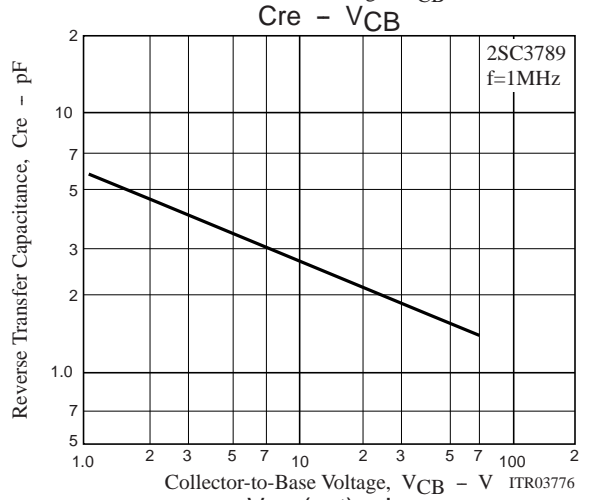
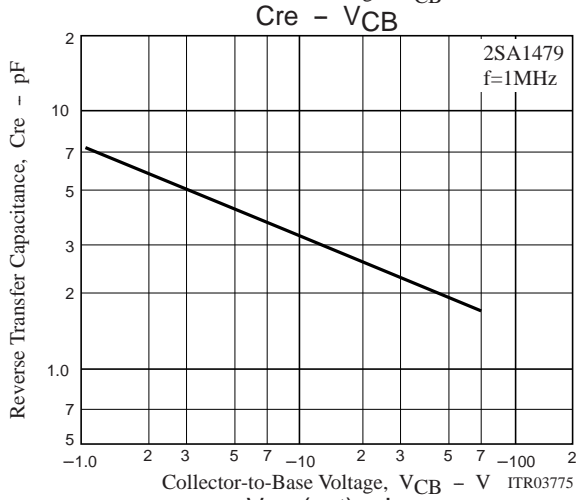
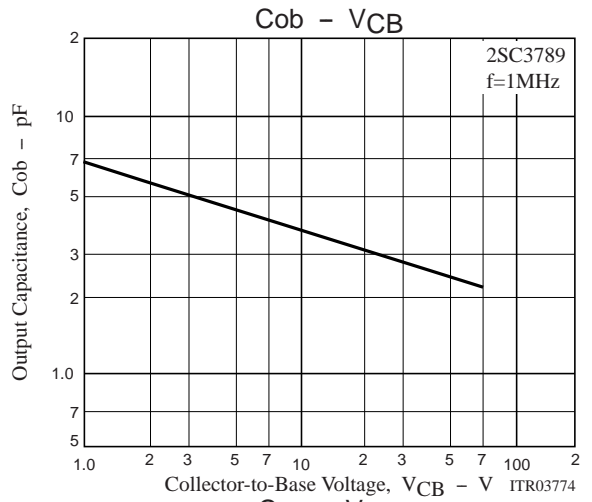
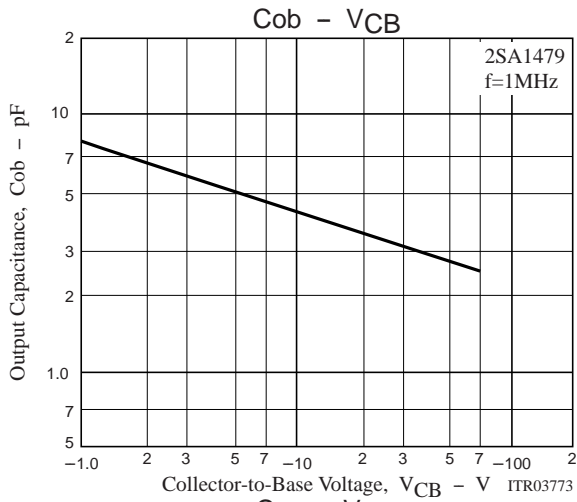
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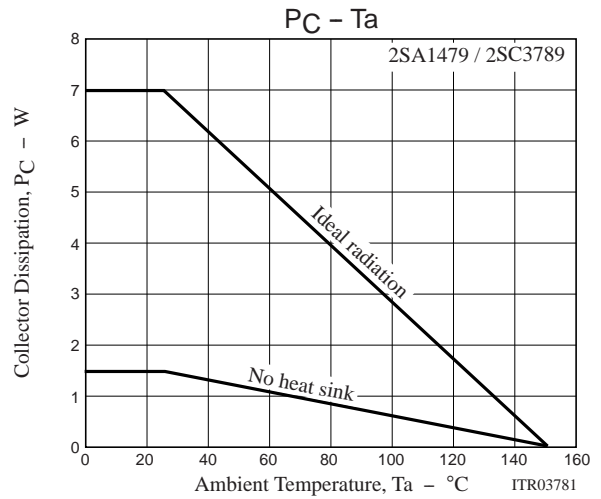
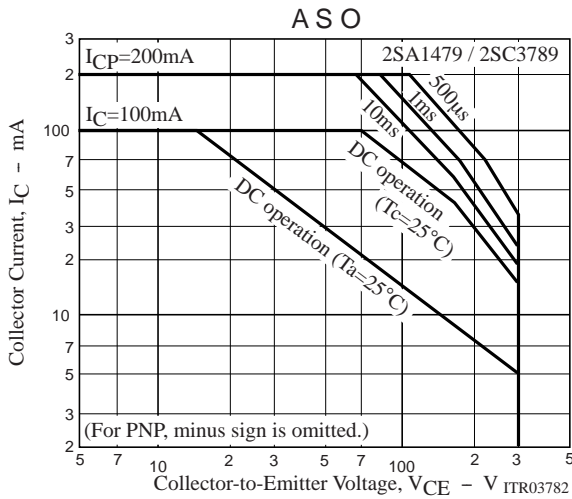


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